

QH03TZ600, QH03BZ600

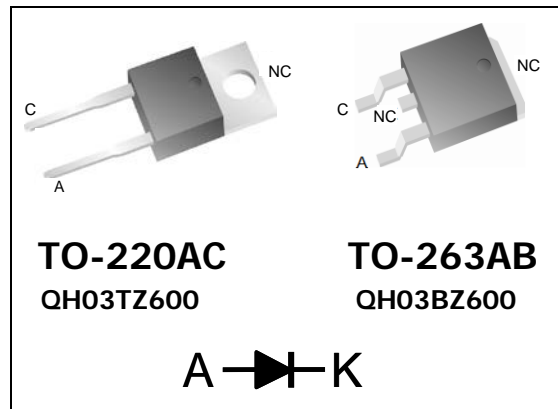
Qspeed™ Family

600 V, 3 A H-Series PFC Diode

Product Summary

$I_{F(AVG)}$	3	A
V_{RRM}	600	V
Q_{RR} (Typ at 125 °C)	14.8	nC
I_{RRM} (Typ at 125 °C)	1.35	A
Softness t_B/t_A (Typ at 125 °C)	1.1	

Pin Assignment



RoHS Compliant

Package uses Lead-free plating and Green mold compound.

Halogen free per IEC 61249-2-21.

General Description

This device has the lowest Q_{RR} of any 600 V silicon diode. Its recovery characteristics increase efficiency, reduce EMI and eliminate snubbers.

Applications

- Power Factor Correction (PFC) boost diode
- Motor drive circuits
- DC-AC Inverters

Features

- Low Q_{RR} , low I_{RRM} , low t_{RR}
- High dI_F/dt capable (1000 A / μ s)
- Soft recovery

Benefits

- Increases efficiency
 - Eliminates need for snubber circuits
 - Reduces EMI filter component size & count
- Enables extremely fast switching

Absolute Maximum Ratings

Absolute maximum ratings are the values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Symbol	Parameter	Conditions	Rating	Units
V_{RRM}	Peak repetitive reverse voltage	$T_J = 25\text{ °C}$	600	V
$I_{F(AVG)}$	Average forward current	$T_J = 150\text{ °C}, T_C = 120\text{ °C}$	3	A
I_{FSM}	Non-repetitive peak surge current	60 Hz, $\frac{1}{2}$ cycle, $T_C = 25\text{ °C}$	35	A
I_{FSM}	Non-repetitive peak surge current	$\frac{1}{2}$ cycle of $t = 28\text{ }\mu$ s Sinusoid, $T_C = 25\text{ °C}$	350	A
T_J	Operating junction temperature range		-55 to 150	°C
T_{STG}	Storage temperature		-55 to 150	°C
	Lead soldering temperature	Leads at 1.6 mm from case, 10 sec	300	°C
V_{ISOL}	Isolation voltage (leads-to-tab)	AC, TO-220	2500	V
V_{ISOL}	Isolation voltage (leads-to-tab)	AC, TO-263	1500	V
P_D	Power dissipation	$T_C = 25\text{ °C}$	30.4	W

Thermal Resistance

Symbol	Resistance from:	Conditions	Rating	Units
$R_{\theta JA}$	Junction to ambient	TO-220 (only)	62	°C/W
$R_{\theta JC}$	Junction to case		4.1	°C/W

Electrical Specifications at $T_J = 25\text{ °C}$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
DC Characteristics							
I_R	Reverse current	$V_R = 600\text{ V}, T_J = 25\text{ °C}$	-	-	250	μA	
		$V_R = 600\text{ V}, T_J = 125\text{ °C}$	-	0.22	-	mA	
V_F	Forward voltage	$I_F = 3\text{ A}, T_J = 25\text{ °C}$	-	2.52	3.0	V	
		$I_F = 3\text{ A}, T_J = 150\text{ °C}$	-	2.1	-	V	
C_J	Junction capacitance	$V_R = 10\text{ V}, 1\text{ MHz}$	-	11	-	pF	
Dynamic Characteristics							
t_{RR}	Reverse recovery time	$dI/dt = 200\text{ A}/\mu\text{s}$ $V_R = 400\text{ V}, I_F = 3\text{ A}$	$T_J = 25\text{ °C}$	-	9.8	-	ns
			$T_J = 125\text{ °C}$	-	16.1	-	ns
Q_{RR}	Reverse recovery charge	$dI/dt = 200\text{ A}/\mu\text{s}$ $V_R = 400\text{ V}, I_F = 3\text{ A}$	$T_J = 25\text{ °C}$	-	5.8	10	nC
			$T_J = 125\text{ °C}$	-	14.8	-	nC
I_{RRM}	Maximum reverse recovery current	$dI/dt = 200\text{ A}/\mu\text{s}$ $V_R = 400\text{ V}, I_F = 3\text{ A}$	$T_J = 25\text{ °C}$	-	0.93	1.4	A
			$T_J = 125\text{ °C}$	-	1.35	-	A
S	Softness factor = $\frac{t_B}{t_A}$	$dI/dt = 200\text{ A}/\mu\text{s}$ $V_R = 400\text{ V}, I_F = 3\text{ A}$	$T_J = 25\text{ °C}$	-	0.92	-	
			$T_J = 125\text{ °C}$	-	1.1	-	

Note to component engineers: H-Series diodes employ Schottky technologies in their design and construction. Therefore, Component Engineers should plan their test setups to be similar to those for traditional Schottky test setups. (For additional details, see Application Note AN-300.)

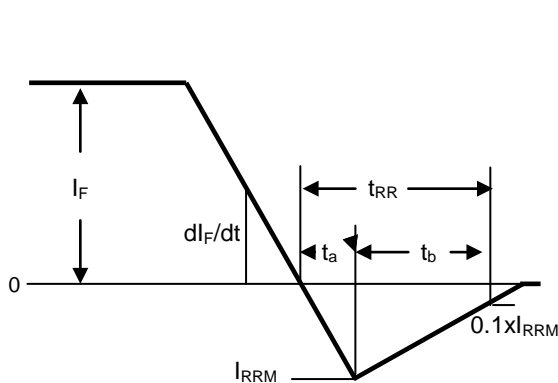


Figure 1. Reverse Recovery Definitions.

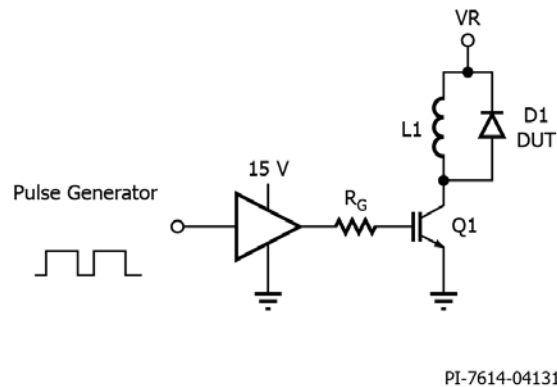


Figure 2. Reverse Recovery Test Circuit.

Electrical Specifications at $T_J = 25\text{ }^\circ\text{C}$ (unless otherwise specified)

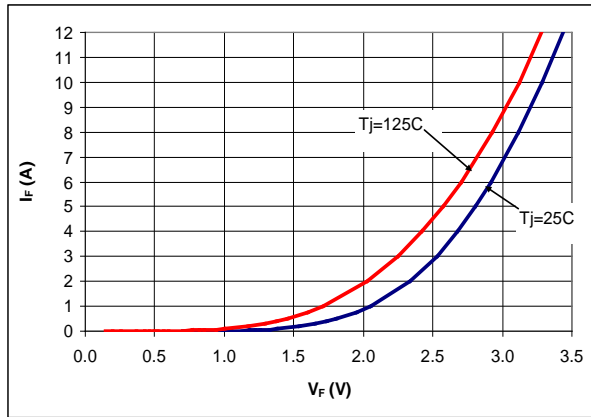


Figure 3. Typical I_F vs. V_F .

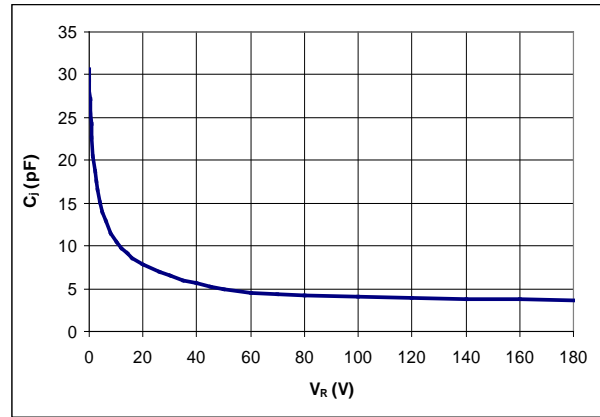


Figure 4. Typical C_J vs. V_R .

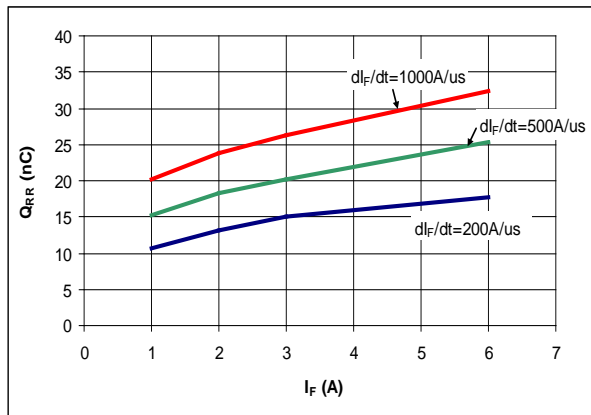


Figure 5. Typical Q_{RR} vs. I_F at $T_J = 125\text{ }^\circ\text{C}$.

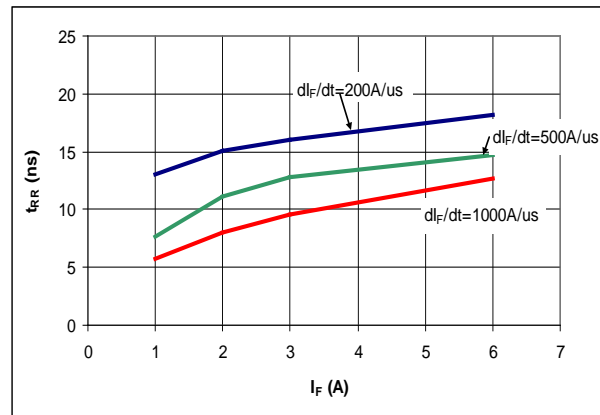


Figure 6. Typical t_{RR} vs. I_F at $T_J = 125\text{ }^\circ\text{C}$.

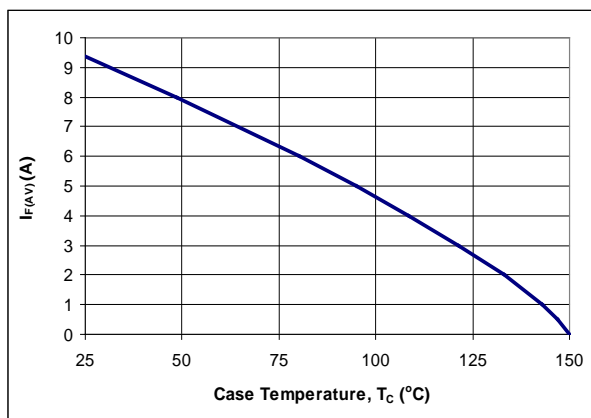


Figure 7. DC Current Derating Curve.

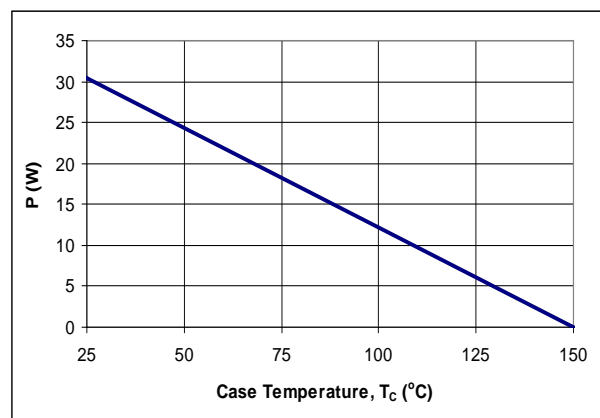


Figure 8. Power Derating Curve.

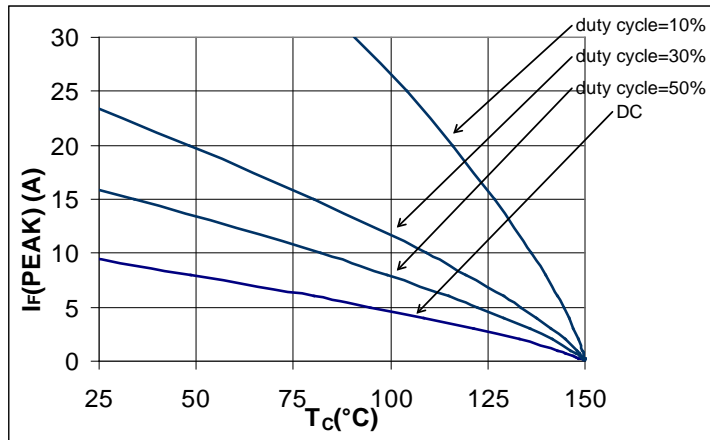


Figure 9. $I_F(\text{PEAK})$ vs. T_C , $f = 70 \text{ kHz}$.

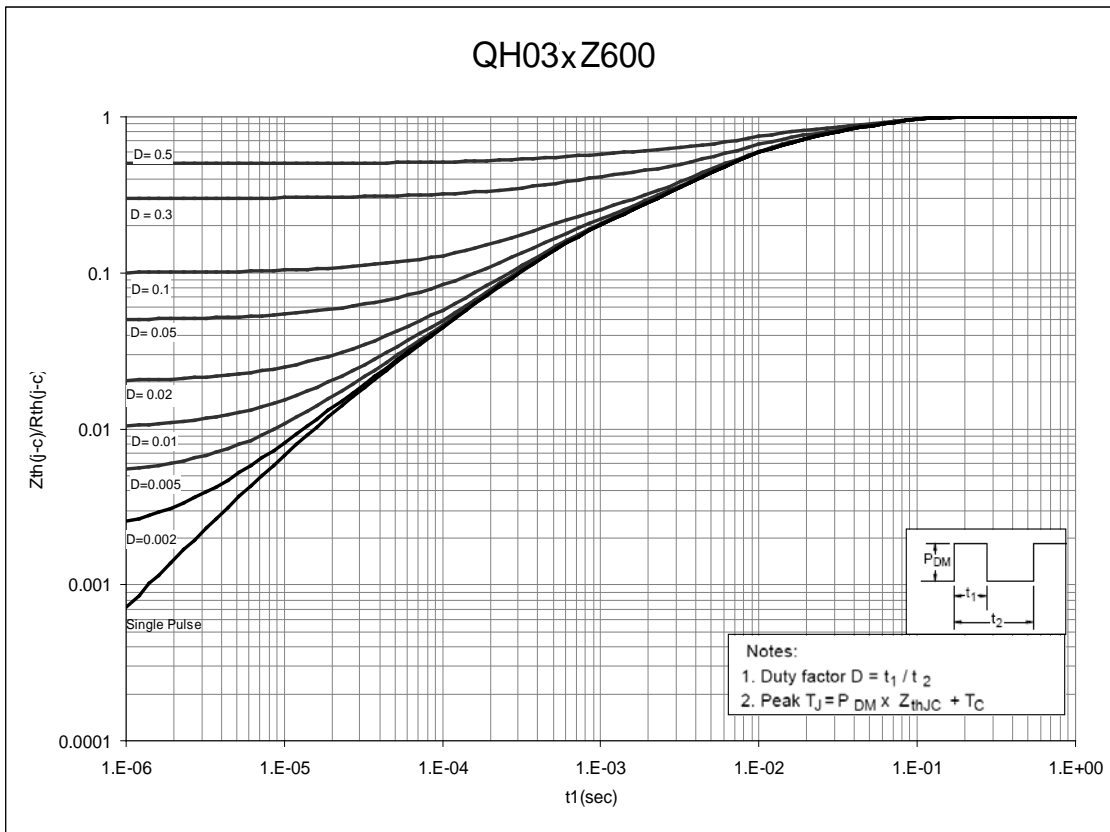
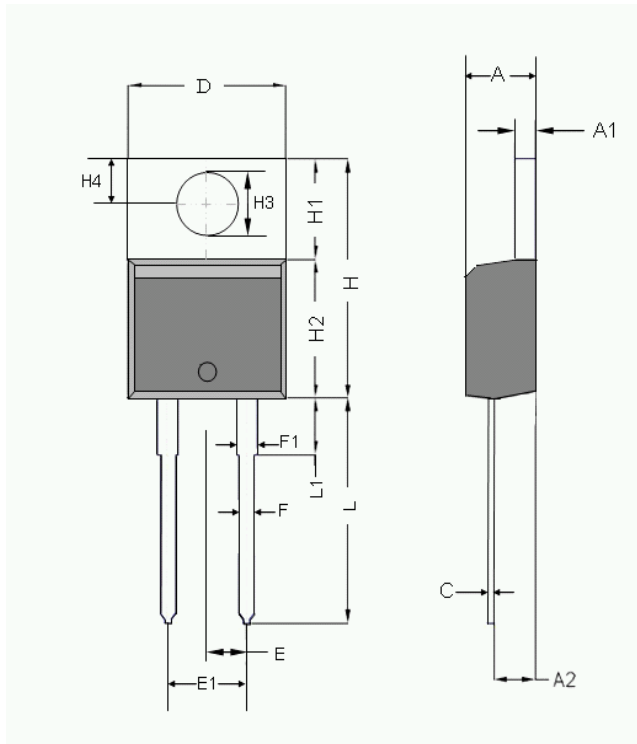


Figure 10. Normalized Maximum Transient Thermal Impedance.

Dimensional Outline Drawing

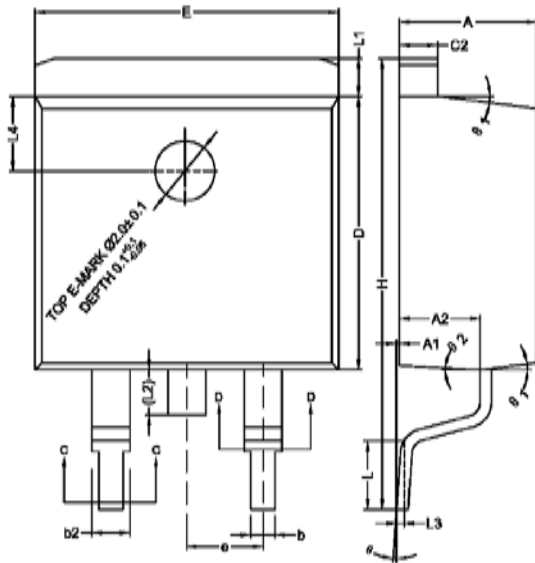
TO-220AC



Dim	Millimeters	
	MIN	MAX
A	4.32	4.70
A1	1.14	1.40
A2	2.03	2.79
C	0.34	0.610
D	9.65	10.67
E	2.49	2.59
E1	4.98	5.18
F	0.508	1.016
F1	1.14	1.78
H	14.71	16.51
H1	5.84	6.795
H2	8.40	9.00
H3	3.53	3.96
H4	2.54	3.05
L	12.70	14.22
L1	-	6.35

Dimensional Outline Drawing

TO-263AB

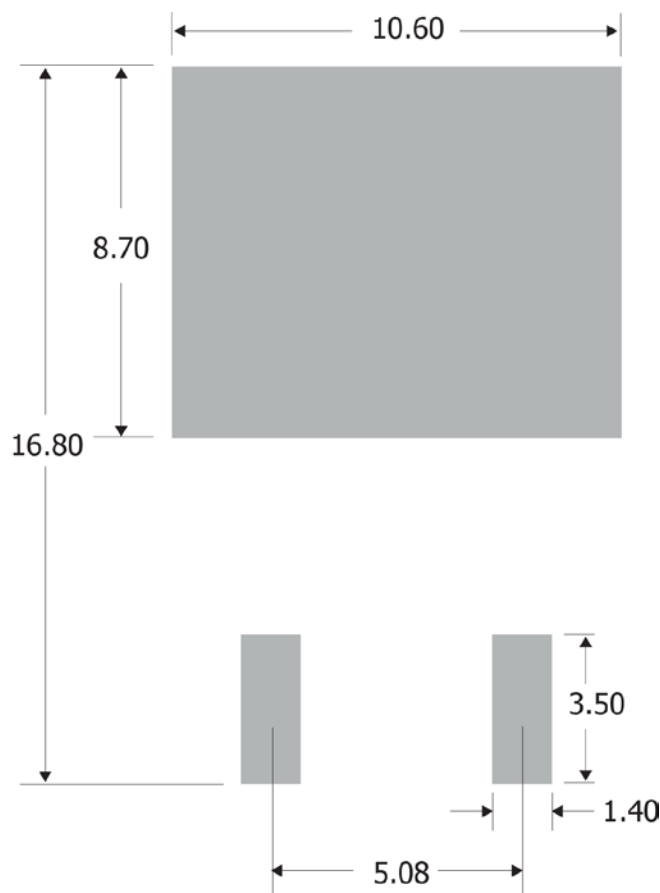


Dim	Millimeters	
	MIN	MAX
A	4.40	4.70
A1	0.00	0.25
A2	2.59	2.79
b	0.77	0.90
b2	1.23	1.36
c2	1.22	1.32
D	9.05	9.25
E	10.06	10.26
e	2.54 BSC	2.54 BSC
H	14.70	15.50
L	2.00	2.60
L1	1.17	1.40
L2	-	1.75
L3	0.25 BSC	0.25 BSC
L4	2.00 BSC	2.00 BSC
θ	0°	8°
θ1	5°	9°
θ2	1°	5°

Mechanical Mounting Method	Maximum Torque / Pressure specification
Screw through hole in package tab	1 Newton Meter (nm) or 8.8 inch-pounds (lb-in)
Clamp against package body	12.3 kilogram-force per square centimeter (kgf/cm ²) or 175 lbf/in ²

Footprint and Solder Pad Dimensions

Pad Dimensions in mm:
TO-263AB



Soldering time and temperature: This product has been designed for use with high-temperature, lead-free solder. The component leads can be subjected to a maximum temperature of 300 °C, for up to 10 seconds. See Application Note AN-303, for more details.

Ordering Information

Part Number	Package	Packing
QH03TZ600	TO-220AB	50 units/tube
QH03BZ600	TO-263AB	800 units/reel

The information contained in this document is subject to change without notice.

Revision	Notes	Date
1.0	Released by Qspeed	01/10
1.1	Converted to Power Integrations Document	01/11
1.2	Added QH03BZ600	02/13
1.3	Updated with new Brand Style. Added footprint and solder pad dimension for TO-263AB package.	11/15

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